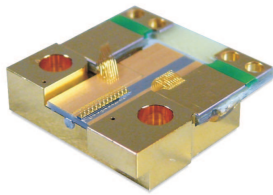


LU0808Fyyy

808nm Multi Emitter Laser Diode on Flat_mount

Up to 21W c.w. or 25W Pulsed Power



Description:

The LU0808F150 series offers high optical output power of up to 21W in c.w. operation from a multi emitter. Long lifetime is ensured due to the Lumics proprietary laser diode facet passivation technology. This performance makes them a valuable tool for the highly efficient medical laser treatment. Further important applications are micro material processing with exceptional power densities and illumination applications.

Features & Functions:

- 2 x 385µm emitter
- 2 x 190µm emitter
- Wavelength 808nm
- Burn-in tested
- Holes for mounting
- Copper base
- Electrically isolated
- Option: FAC lens

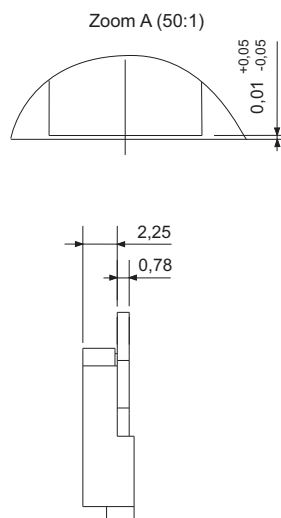
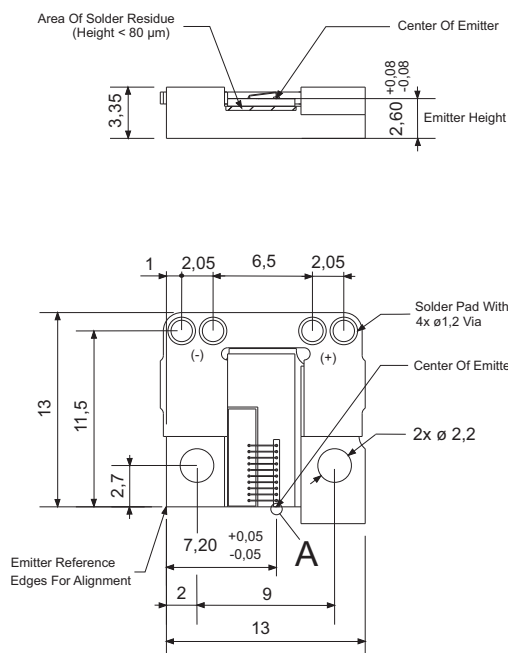
Benefits:

- Small footprint
- High reliability
- Field proven reliability

Applications:

- Pumping (SSL)
- Plastic welding
- Marking
- Illumination
- Medical treatment

Drawing (dimensions in mm)

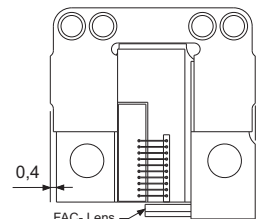


Connections

Contact Pad	Function
(+)	LD Anode (+)
(-)	LD Cathode (-)

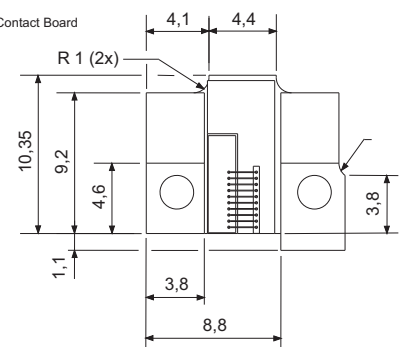
Option

Additional FAC-Lens



Option

Without Contact Board



We manufacture diode lasers.

Typical Electrical and Optical Characteristics

Parameter	Symbol	LU0808F150	Lu0808F210	Unit
Emitter Width	W	2 x 190	2 x 385	µm
Pitch of the 2 emitters		400	140/463	µm
c.w. Operating Power	P _{op (c.w.)}	15	21	W
c.w. Operating Current	I _{op (c.w.)}	17.5	26	A
Pulsed (1) Operating Power	P _{op (< 100µsec pulse / < 10% d.c.)}	25	not applicable	W
Pulsed (1) Operating Current	I _{op (< 100µsec pulse / < 10% d.c.)}	25	not applicable	A
Threshold Current	I _{th}	3600	5000	mA
Forward Voltage	V _{op}	1.8	1.7	V
Slope Efficiency	λ _{diff}	1.15	1.1	W / A
Peak Wavelength	λ _{peak}	808+/-10 (2)	808+/-10 (2)	nm
Spectral Width (FWHM)	λ _{FWHM}	3	3	nm
Beam Divergence (horizontal) ₍₃₎	FWHM, 90% energy inclusion at I _{op}	7	7	deg
Beam Divergence (vertical) ₍₃₎	FWHM, Gaussian beam at I _{op}	25	25	deg
AR Reflectivity ₍₄₎	r _f	2-3	2-3	%
HR Reflectivity	r _r	95	95	%
Spectral Shift with Temp.	λ _{T_Shift}	0.3	0.3	nm / K
Spectral Shift with Current	λ _{P_Shift}	0.4	0.4	nm / A
Operating Temp.	T _{op}	20-30	20-30	°C

Option: FAC lense

Fast axis (vertical) divergence	NA	< 3	< 3	mrاد
Vertical width of the beam		< 0.8	< 0.8	mm

Important Notes:

- (1) Typical pulse condition: pulse <100µsec / d.c. 5%
- (2) 808nm +/-3nm, or other wavelength (793 to 840nm) on request
- (3) The Intensity I(alpha,G,SG) of the far field in vertical and horizontal plane versus deflection angle (alpha) can be approximated with a Zemax Super-Gaussian Diode model by two parameters (first) Gaussian(G) width describing the beam width by the Full Width Half Maximum (FWHM) of the beam intensity in measurement plane and (second) Super Gauss (SG) describing the deviation from a Gaussian shape of the beam whereas:

$$I(\alpha, G, SG) = \exp(-2((\alpha/G)^{2SG}))$$
with $G(\text{FWHM}) = \text{FWHM} / (2 \cdot \sqrt[SG]{0.346573})$
Lateral far field: Typical parameter values are SG = 3-4 and G(7°) ~ 6. Due to the non - gaussian shape the FWHM of the beam includes app. 90% of the energy. The beam width increase by current with app. 0.4° / A.
Vertical far field: Typical parameter values are SG = 1 and G(25°) ~ 21. The beam width does not change by current.
- (4) Optionally other coatings are offered on request

Absolute Maximum Ratings

Parameter	Symbol	LU0808F150	LU0808F210	Unit
LD c.w. Forward Current	I _{op, (c.w.) max}	20	30	A
LD pulsed (<100µsec, <10% d.c.) Forward Current	I _{op, (pulsed) max}	28	-	A
LD Reverse Voltage	V _{R, max}	2	2	V
Maximum Processing Temperatures:				
Solder pads for LD contacts / max 5sec.	T _{Op max, solder pad}	250	250	°C
Soldering of Cu base block / max 5sec.	T _{Op max, Cu base}	150	150	°C
Rel. Humidity, Storage Temperature and Operating Heat Sink Temperature ₍₁₎				

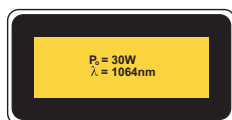
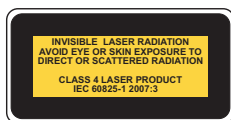
Note:

Absolute Maximum Ratings may be applied to the laser module for short period of time only. Exposure to maximum ratings for extended period of time or exposure above one or more max ratings may cause damage or affect the reliability of the device.

Operating Temperature and Rel. Humidity must be chosen such that the dewpoint of humid air around the laser diode is below the operating heat sink temperature to avoid condensing of water on the laser diode facet.

This product contains 1.5% BeO as solid fully metallized ceramic (CAS Number 1304-56-9), 0.05% of solid metallized InAlGaAsP crystal, as well as 0.05% Pb (CAS Nummer 7439-92-1)

User Safety



We manufacture diode lasers.